

# Effect of Chemically Treated Aluminum Nitrate: Its Dielectric Studies of Sisal Fiber Composite

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**Abstract:** Aluminum oxide synthesized through sintering route. The present research work deals with Alrrite composite prepared using chemical reactions. Aluminum nitrates and ammonium chloride doped with sisal fiber has been prepared. The comparative studies of aluminum oxide were examined through dielectric measurement.

**Keywords:**  $\alpha$ - $\text{Al}_2\text{O}_3$ , sintering method, dielectric measurement.

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## 1. INTRODUCTION

Aluminum oxides are chemical compounds composed of aluminum and oxygen. All together, there are sixteen known aluminum oxides and oxyhydroxides. [1-2] Aluminum (III) oxide or aluminum oxide is the inorganic compound with the formula  $\text{Al}_2\text{O}_3$ . Powder metallurgy comprises a set of processes of forming having for common denominator a raw material in a powder form. The reduced aluminum powder is the most widely used material in powder metallurgy industry.  $\text{LiAlO}_2$  has various crystalline structures such as  $\alpha$ - $\text{LiAlO}_2$ ,  $\beta$ - $\text{LiAlO}_2$ ,  $\gamma$ - $\text{LiAlO}_2$ , Layered  $\text{LiAlO}_2$ , Corrugated  $\text{LiAlO}_2$ , Goethite type  $\text{LiAlO}_2$  etc. The crystalline structure of  $\text{LiAlO}_2$  depends mainly on the preparation methods. Many researches prepared  $\text{LiAlO}_2$  with different structures. V.R. Galakhov et al. prepared  $\alpha$ - $\text{LiAlO}_2$  with Fm-3m space group by using solid state reaction and M. Tabuchi et al. prepared  $\alpha$ - $\text{LiAlO}_2$  with Fm3m space group by hydrothermal synthesis [3-5].

Similarly,  $\beta$ - $\text{LiAlO}_2$ ,  $\gamma$ - $\text{LiAlO}_2$  and layered  $\text{LiAlO}_2$  are prepared by hydrothermal synthesis and other methods. Corrugated  $\text{LiAlO}_2$  and Goethite type  $\text{LiAlO}_2$  are prepared by ion exchange method. In comparison with the conventional solid phase synthesis methods, hydrothermal method is one of the simplest and best methods to prepare lithium based cathode materials [6-9]. In case of the electrical properties of the oxides, grain boundaries play an important role. The measurement of conductivity and permittivity shows dispersion behavior which offers an opportunity to gain some information of ionic migration process. Considering the significance, the electrical conductivity studies on various lithium-based oxides such as  $\text{LiCoO}_2$ ,  $\text{LiCeO}_2$ ,  $\text{LiSmO}_2$ ,  $\text{Li}_2\text{SnO}_3$ ,  $\text{Li}_2\text{MnO}_3$ ,  $\text{LiMn}_2\text{O}_4$ , and  $\text{Li}_2\text{V}_2\text{O}_5$ , and others have been reported in the literature [10-13]. However, to the best of our knowledge, there are meager reports on electrical and dielectric properties of  $\text{LiAlO}_2$ . A detailed study on the temperature and frequency dependent electrical properties is necessary to understand the conduction mechanism in  $\text{LiAlO}_2$  for effective utilization as cathode material in the fabrication of lithium ion batteries.

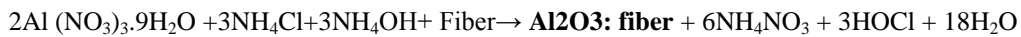
In the oxides of aluminum  $\alpha$ - $\text{Al}_2\text{O}_3$  is the most stable compound. For the non-existence of  $\text{Al}^{++}$  ions  $\alpha$ - $\text{Al}_2\text{O}_3$  has higher electrical resistivity than other oxides of aluminum such as  $\text{Al}_3\text{O}_4$ ,  $\text{AlO}$ , and Alrrites. It has been reported, however, that at the temperature above  $1200^\circ\text{C}$  there is the possibility of the appearance of  $\text{Al}^{++}$  ions in  $\alpha$ - $\text{Al}_2\text{O}_3$ . When the oxides contain Alrrous ions, the hopping of electrons between Alrrous and aluminum ions gives rise to higher conductivity. Thus for samples possessing both the conductive and less-conductive phases the Maxwell-Wagner interfacial polarizations are observed. With the surface modified by the use of mild reducing condition of sintering Hirbon reported the interfacial polarization in the sintered compacts of  $\alpha$ - $\text{Al}_2\text{O}_3$ . On the other hand, in  $\alpha$ - $\text{Al}_2\text{O}_3$  containing other ions of different valences such as  $\text{Ti}^{++}$  ions polarizations due to permanent dipoles of  $\text{Al}^{++}\text{-Al}^{+++}$  induced by  $\text{Ti}^{+4}$  ions were observed at very low temperature [14-18]

## 2. MATERIAL AND METHOD

### 2.1: Chemical treatment of fiber:

Aluminum Nitrate ( $\text{Al}(\text{NO}_3)_3 \cdot 9\text{H}_2\text{O}$ ) and ammonium chloride ( $\text{NH}_4\text{Cl}$ ) was taken in the ratio 10:4 in 500 ml of distilled water. The mixture was stirred till a homogenous solution was obtained. In this mixture 10g of sisal fiber was added and then 1:1 solution of  $\text{NH}_4\text{OH}$  (liquid ammonia) was added to it then left the solution for one hour. Again the mixture thus obtained was dried and then annealed in muffle furnace at  $1000^\circ\text{C}$  and kept it at that temperature for 15 min.

The reaction may take place in this way



When aluminum nitrate reacts with ammonium chloride and ammonium hydroxide along with sisal fiber at  $1000^\circ\text{C}$  with ammonium nitrate and HO-Cl (hypochlorous acid) decomposed at such high temperature and only **aluminum oxide** is left.

### 2.2: Nature and structure of sample after firing:

The material formed was found to in **solid crystals** in physical appearance. The sample appeared in powder form and it is like **Cole** in color.

## 3. RESULT AND DISCUSSION

The electrical properties of the insulating material  $\text{Al}_2\text{O}_3$  composite were measured by impedance analyzer these dielectric measurement of  $\text{Al}_2\text{O}_3$  composite doped with sisal fiber shown in fig 1-3 and 4-6. In the Fig 1 represents the graph between frequency and  $\tan\delta$  and fig 2 shows the comparison between frequency and  $\epsilon$ .

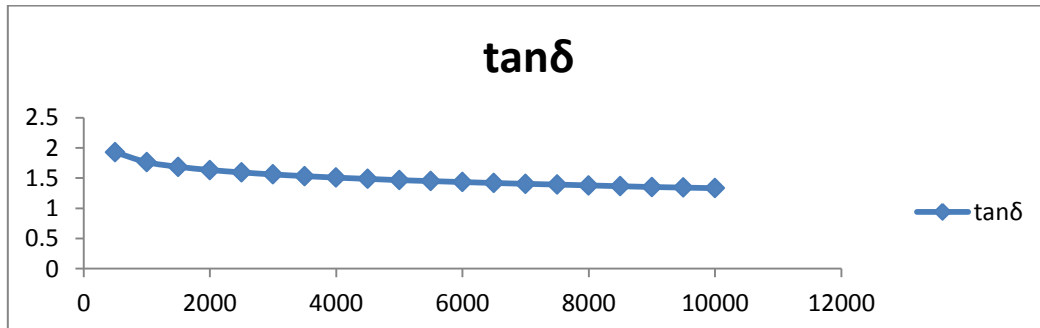


Fig 1

The dielectric constant  $\epsilon$  and loss  $\tan\delta$  of  $\text{Al}_2\text{O}_3$  at room temperature  $30^\circ\text{C}$  are measured to be 1.9 to 1.3 respectively and are found to decrease with the increase in the frequency. The value of  $\epsilon$  and  $\tan\delta$  are found to differ with each other. In fig 1 the variation of dielectric constant at different frequencies with room temperature  $30^\circ\text{C}$  for  $\text{Al}_2\text{O}_3$  is shown that it decreases considerably with increase in frequency.

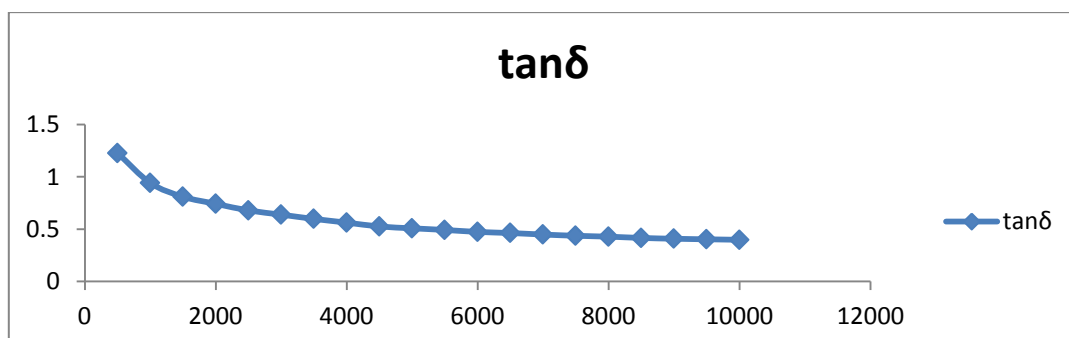


Fig 2

This dielectric dispersion is attributed to the Maxwell and Wagner type of interfacial polarization in agreement with Koop's phenomenological theory [19]. Since polarization decreases with increasing frequency and reaches constant values, a decrease in dielectric constant with frequency is observed.

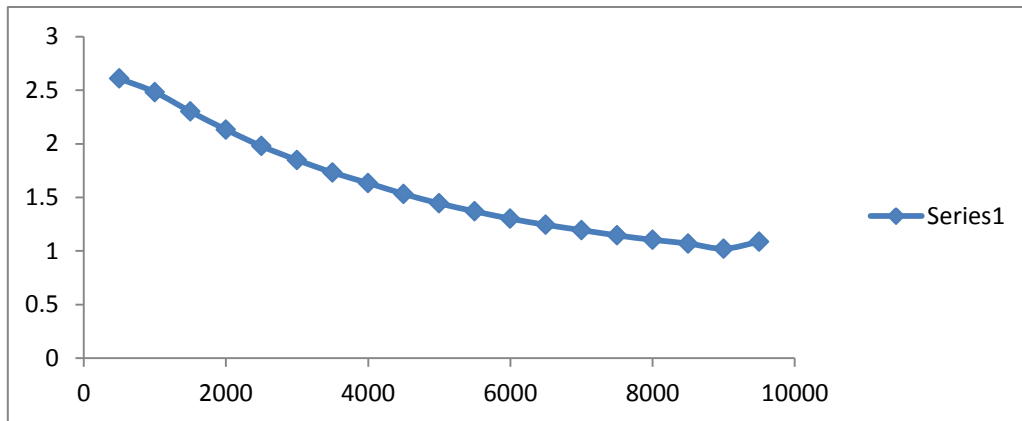


Fig 3

At lower frequencies, dielectric loss  $\tan\delta$  is large and it decreases with increasing frequency. The  $\tan\delta$  is the energy dissipation in the dielectric system, which is proportional to the imaginary part of the dielectric constant. An increase in loss factor at higher frequencies may be due to the series resistance of the electrodes, leads, etc [20-22].

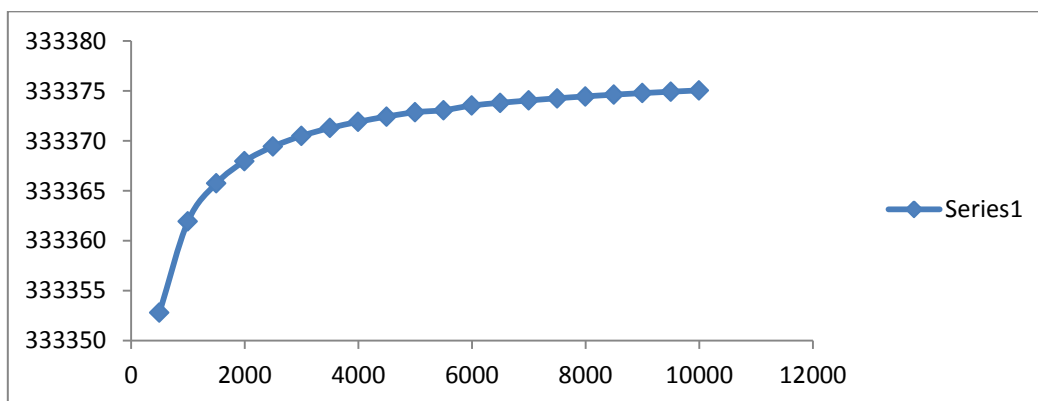


Fig 4

While in fig 4, 5 & 6 is a comparison plot of variation of dielectric constant with different frequency at constant temperature shows an increase considerably with increase in frequency. It was observed from these figures that the dielectric constant increases continuously with increase in frequency for all the samples, followed with a frequency independent behavior.

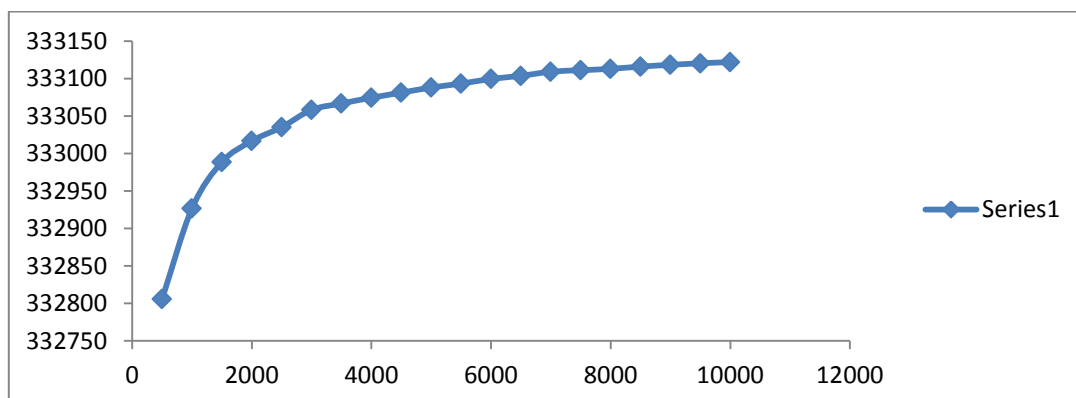


Fig 5

The dielectric properties of Alumina are dependent upon several factors, including the method of preparation, chemical composition and grain structure, size and natural fiber (sisal fiber) and it's contains cellulose, hemicelluloses, lignin and pectin. The observed dielectric behavior of our samples may also be due to the particle size effect and is also in concurrence with observation made by other Investigators [23-24]. The effect of electrical homogeneity fine grain structure and shape of the Alumina samples affect the dielectric properties [25]. It also presence the  $\alpha$  impurities contributes towards the change in dielectric properties. The dielectric constant of 25-30 at 10 KHz and an increasing trend is observed at higher frequencies. This is normal behavior for high density fine chemically homogenous material [26].

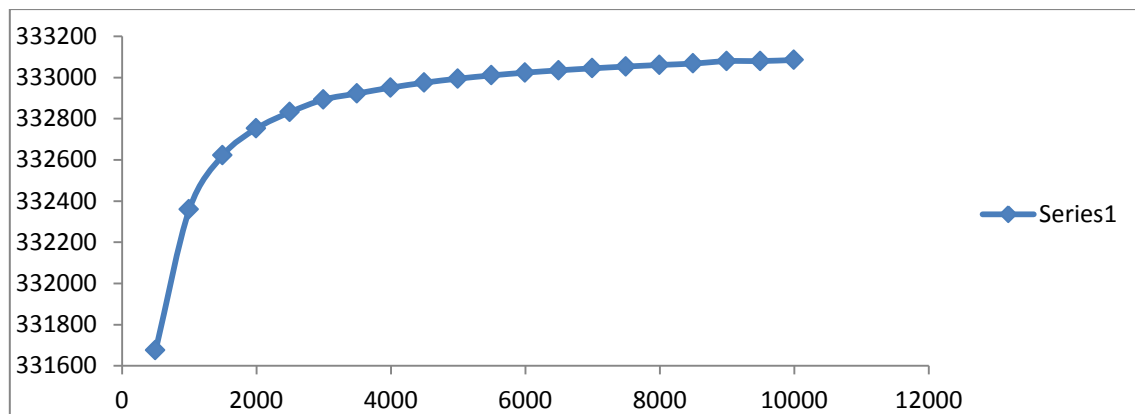


Fig 6

The electronic exchange between Ammonium and aluminum ions didn't follow the path of frequency which is externally applied alternating beyond the critical frequency value. The dielectric behavior of samples which shown in graphs is because of its particle size effect [27]. If  $\epsilon$  remains unaffected with increase in temperature then frequency also remains the same, which means that the local carriers are immobile. It is understood that the local charge carriers are immobile and the thermal activation is negligible. This further suggests that the samples possess a high chemical homogeneity and fine grain distribution. The presence of moisture, cellulose, hemicelluloses, lignin and pectin is also indicated by the electrical conductivity results. It is reported the presence of moisture plays an important role in the formation and stabilization of  $Al_2O_3$  [28].

#### 4. CONCLUSION

The effect of chemical homogeneity, fine grain structure, particle size and shape of the Alumina samples are understood to affect the properties of dielectric behavior. The presence of moisture, cellulose, hemicelluloses, lignin and pectin also contribute towards changes in dielectric properties.

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